



US 20240244836A1

(19) **United States**

(12) **Patent Application Publication**  
**Yamaguchi et al.**

(10) **Pub. No.: US 2024/0244836 A1**

(43) **Pub. Date: Jul. 18, 2024**

(54) **SEMICONDUCTOR DEVICE AND METHOD  
FOR FORMING THE WIRING STRUCTURES  
AVOIDING SHORT CIRCUIT THEREOF**

**Publication Classification**

(51) **Int. Cl.**  
**H10B 12/00** (2006.01)

(52) **U.S. Cl.**  
**CPC** ..... **H10B 12/50** (2023.02); **H10B 12/0335**  
(2023.02); **H10B 12/053** (2023.02); **H10B**  
**12/09** (2023.02); **H10B 12/315** (2023.02);  
**H10B 12/34** (2023.02)

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(21) Appl. No.: **18/622,235**

(22) Filed: **Mar. 29, 2024**

**Related U.S. Application Data**

(62) Division of application No. 17/355,006, filed on Jun.  
22, 2021, now abandoned.

(57) **ABSTRACT**

A semiconductor device includes: a substrate; a memory cell region over the substrate; a peripheral region over the substrate, the peripheral region being adjacent to the memory cell region; and a plurality of first and second word-lines extending across the memory cell region and the peripheral region; wherein the plurality of first word-lines and the plurality of second word-lines are arranged alternately with each other; and wherein the length of the first word-line in the peripheral region is longer than the length of the second word-line in the peripheral region.

